RL78 FAMILY HARDWARE MANUAL GUIDE - ELECTRICAL CHARACTERISTICS EDITION

JULY 2023 RENESAS ELECTRONICS CORPORATION



ABSOLUTE MAXIMUM RATINGS 1

Supply voltage	VDD EVDD0, EVDD1 EVSS0, EVSS1	EVDD0 = EVDD1 EVSS0 = EVSS1	-0.5 to +6.5 -0.5 to +6.5	V V
REGC pin input voltage	EVsso, EVss1			V
REGC pin input voltage		EVss0 = EVss1	0 E to 10 2	
REGC pin input voltage			-0.5 to +0.3	V
	VIREGC	REGC	-0.3 to +2.1 and -0.3 to V _{DD} + 0.3 ^{Note 1}	V
Input voltage	VI1	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P140 to P147	-0.3 to EVDD0 + 0.3 and -0.3 to VDD + 0.3Note 2	V
	VI2	P60 to P63 (N-ch open-drain)	-0.3 to +6.5	V
	VI3	P20 to P27, P121 to P124, P137, P150 to P156, EXCLK, EXCLKS, RESET	-0.3 to VDD + 0.3Note 2	V
		V12 V13	P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P140 to P147 Vi2 P60 to P63 (N-ch open-drain) Vi3 P20 to P27, P121 to P124, P137, P150 to P156, EXCLK, EXCLKS, RESET	P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P140 to P147 and -0.3 to VDD + 0.3Note 2 VI2 P60 to P63 (N-ch open-drain) -0.3 to +6.5 VI3 P20 to P27, P121 to P124, P137, -0.3 to VDD + 0.3Note 2

information regarding electrical characteristics. In order to use it correctly, it is necessary to confirm these conditions as well.

Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.

 Guaranteed values of characteristics and values that users should adhere to
 Guaranteed value of characteristics



$\textbf{ABSOLUTE MAXIMUM RATINGS} \ \textbf{(2)}$

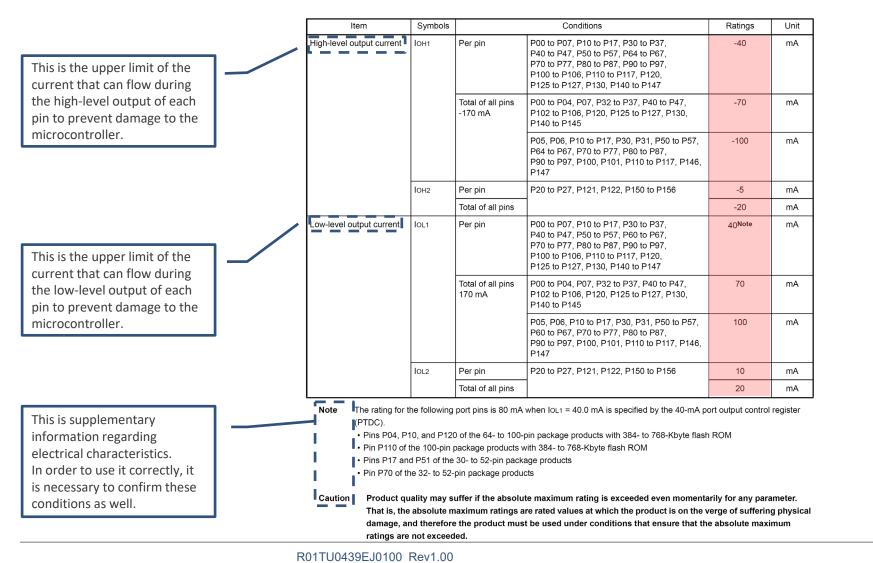
This is the output voltage	_	Item	Symbols	Conditions	Ratings	Unit
range for each pin that will not damage the microcontroller.		Output voltage	Vo1	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P60 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P130, P140 to P147	-0.3 to EVDD0 + 0.3 and -0.3 to VDD + 0.3Note 2	V
This is the input voltage range			Vo2	P20 to P27, P121, P122, P150 to P156	-0.3 to VDD + 0.3Note 2	V
for the analog pin that will not damage the microcontroller.		Analog input voltage	VAI1	ANI16 to ANI26	-0.3 to EVDD0 + 0.3 and -0.3 to AVREFP + 0.3 Notes 2, 3	V
			VAI2	ANI0 to ANI14	-0.3 to VDD + 0.3 and -0.3 to AVREFP + 0.3 Notes 2, 3	V
This is supplementary information regarding electrical characteristics. In order to use it correctly, it is necessary to confirm these conditions as well.		Caution Product That is, t	on a pin in use for quality may suffe he absolute max	r than 6.5 V. A/D conversion must not exceed AVREFP + 0.3. It if the absolute maximum rating is exceeded imum ratings are rated values at which the pro e product must be used under conditions tha	d even momentarily for any paran oduct is on the verge of suffering	physical

ratings are not exceeded.

 Guaranteed values of characteristics and values that users should adhere to
 Guaranteed value of characteristics
 Explanation subject



ABSOLUTE MAXIMUM RATINGS ③



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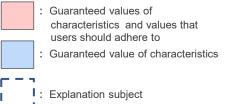
Item	Symbols	Condition	S	Ratings	Unit
Ambient operating	Та	In normal operation mode	3C: Industrial applications	-40 to +105	°C
temperature			-40 to +85		
		In flash memory programming mode	3C: Industrial applications	-40 to +105	
			2D: Consumer applications	-40 to +85	
Storage temperature	Tstg		•	-65 to +150	°C

Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.

This is supplementary information regarding electrical characteristics. In order to use it correctly, it is necessary to confirm these conditions as well.

This is the temperature range for storage without operating

the microcontroller.

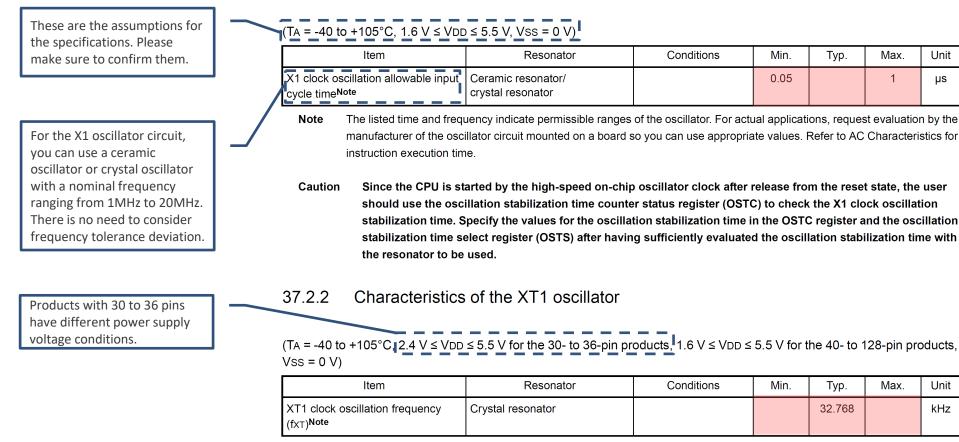




CHARACTERISTICS OF THE OSCILLATORS

CHARACTERISTICS OF X1 AND XT1 OSCILLATORS

37.2.1 Characteristics of the X1 oscillator



The listed time and frequency indicate permissible ranges of the oscillator. For actual applications, request evaluation by the Note manufacturer of the oscillator circuit mounted on a board so you can use appropriate values. Refer to AC Characteristics for instruction execution time.

Min.

0.05

Min.

Typ.

32.768

Max.

Unit

kHz

Typ.

Max.

Unit

μs

Guaranteed values of characteristics and values that users should adhere to Guaranteed value of characteristics



CHARACTERISTICS OF THE OSCILLATORS

CHARACTERISTICS OF THE ON-CHIP OSCILLATORS

37.2.3 Characteristics of the On-chip Oscillators

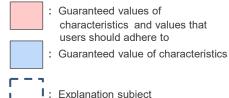
	Item	Symbol		Condition	S	Min.	Тур.	Max.	Unit
	High-speed on-chip oscillator clock frequency	fін				1		32	MHz
This is the accuracy range of	High-speed on-chip		HIPREC = 1	+85 to +105°C	1.8 V ≤ VDD ≤ 5.5 V	-2.0		+2.0	%
the clock frequency for the high-speed on-chip oscillator.	oscillator clock frequency accuracy ^{Note} 1				1.6 V ≤ VDD ≤ 5.5 V	-6.0		+6.0	%
The operation of the CPU and				-20 to +85°C	1.8 V ≤ VDD ≤ 5.5 V	-1.0		+1.0	%
peripheral functions depends on the accuracy of the selected operating clock.					1.6 V ≤ VDD ≤ 5.5 V	-5.0		+5.0	%
				-40 to -20°C	$1.8 \text{ V} \leq \text{VDD} \leq 5.5 \text{ V}$	-1.5		+1.5	%
					$1.6 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}$	-5.5		+5.5	%
By adjusting the High-Speed			HIPREC = 0N	lote 4		-15		0	%
On-Chip Oscillator Trimming Register (HIOTRM), fIH can be corrected. It indicates the	High-speed on-chip loscillator clock correction resolution						0.05		%
frequency accuracy that	Note 1. The accuracy va	alues were ob	tained in testing	n of this product					. <u> </u>

 $(TA = -40 \text{ to } +105^{\circ}\text{C}, 1.6 \text{ V} \le \text{VDD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

- Note 1. The accuracy values were obtained in testing of this product.
- Note 2. The listed values only indicate the characteristics of the oscillators. Refer to AC Characteristics for instruction execution time.

Note 3. Guaranteed by characterization results.

Note 4. The listed condition applies when the setting of the FRQSEL3 bit is 1.



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1.

changes when the setting

value of HIOTRM is varied by

DC CHARACTERISTICS PIN CHARACTERISTICS ①

This is the upper limit of the	 Item	Symbol	Conditions		Min.	Тур.	Max.	Unit
current that can flow during the high-level output of each oin. Please limit the current with external circuitry to not exceed this value.	Allowable high-level output currentNote 1	IOH1	Per pin for P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P130, P140 to P147	1.6 V ≤ EVDD0 ≤ 5.5 V	WIIII.	iyp.	-10.0 Note 2	mA
urrent that can flow per pin.			Total of P00 to P04, P07, P32 to P37, P40 to P47,	4.0 V ≤ EVDD0 ≤ 5.5 V			-55.0 Note 4	mA
		Τ	P102 to P106, P120, P125 to P127, P130,	2.7 V ≤ EVDD0 < 4.0 V			-10.0	mA
This is the total upper limit of			P140 to P145	1.8 V ≤ EVDD0 < 2.7 V			-5.0	mA
he current that can flow			(when duty ≤ 70% Note 3)	1.6 V ≤ EVDD0 < 1.8 V			-2.5	mA
through the relevant pins. 'Duty ≤ 70%" indicates the percentage of time during			Total of P05, P06, P10 to P17, P30, P31, P50 to P57, P64 to P67,	$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V}$			-80.0 Note 5	mA
which the current can flow.			P70 to P77, P80 to P87, P90 to P97, P100, P101,	2.7 V ≤ EVDD0 < 4.0 V			-19.0	mA
			P110 to P117, P146, P147	1.8 V ≤ EVDD0 < 2.7 V			-10.0	mA
			(when duty ≤ 70% ^{Note 3})	1.6 V ≤ EVDD0 < 1.8 V			-5.0	mA
			Total of all pins (when duty ≤ 70% ^{Note 3})	1.6 V ≤ EVDD0 ≤ 5.5 V			-135.0 Note 6	mA

(Notes, Caution, and Remark continue on the next page.)

haracteristics and values that sers should adhere to Guaranteed value of characteristics



DC CHARACTERISTICS 2

	Item	Symbo	Conditi	ons	Min.	Тур.	Max.	Unit	
	Allowable high-level output currentNote 1	Іон2	Per pin for P20 to P27, P121, P122, P150 to P156	4.0 V ≤ VDD ≤ 5.5 V			-3.0 Note 2	mA	
				2.7 V ≤ V _{DD} < 4.0 V			-1.0 Note 2	mA	
				1.8 V ≤ VDD < 2.7 V			-1.0 Note 2	mA	
				1.6 V ≤ VDD < 1.8 V			-0.5 Note 2	mA	
The current value that can			Total of all pins	4.0 V ≤ VDD ≤ 5.5 V			-20.0	mA	
flow depends on the			(when duty ≤ 70% ^{Note 3})	2.7 V ≤ VDD < 4.0 V			-10.0	mA	
conditions of VDD.				1.8 V ≤ VDD < 2.7 V			-5.0	mA	
				1.6 V ≤ VDD < 1.8 V			-5.0	mA	
	output pin.		uaranteed at the listed currents ev				VDD pin t	o an	
When using with a duty > 70%			hese and other pins must also not oply when the duty cycle is no grea				ate the ou	tput	
condition, the current value that can flow becomes smaller.	current wh	en the dut	y cycle is greater than 70%, where	n is the duty cycle.					
The average current that can		•	It from the listed pins = $(IOH \times 0.7)/$: 80% and IOH = -10.0 mA	(n × 0.01)					
flow remains unchanged.		•	It from the listed pins = (-10.0×0.7)	, , , , , , , , , , , , , , , , , , ,					
			cycle has no effect on the current to n rating must not flow into a single		single pin.	A current h	igher thar	n the	
			is -30 mA in the products for indus		x3Cxx) wit	h an ambie	ent operat	ing	
The current value is different	temperatur	e range of	f 85°C to 105°C.						
when products for industrial			is -50 mA in the products for indus f 85°C to 105°C.	trial applications (R7F100Gx	x3Cxx) wit	h an ambie	ent operat	ing	: Guaranteed values of
applications are used in the			are respectively -100 mA and -60	mA in the products for indust	trial applica	tions (R7F	100Gxx30	Cxx) with	characteristics and values that users should adhere to
temperature range of -40°C to 105°C.	L 💻 🚽 an ambien	t operating	temperature range of -40°C to 85	°C and of 85°C to 105°C.					: Guaranteed value of characterist
		02 to P04,	ns are not capable of the output P10 to P15, P17, P34, P42 to P4		-			, and	Explanation subject

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DC CHARACTERISTICS PIN CHARACTERISTICS ③

	Item	Symbol	Conditions		Min.	Тур.	Max.	Unit
This is the upper limit of the current that can flow during the low-level output of each pin. Please limit the current with external circuitry to meet this specification.	Allowable low-level output currentNote 1	IOL1	Per pin for P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P130, P140 to P147				20.0 Notes 2, 3	mA
			Per pin for P60 to P63				15.0 Note 2	mA
This is the upper limit of the current that can flow per pin.			Total of P00 to P04, P07, P32 to P37, P40 to P47,	$4.0 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}$			70.0 Note 5	mA
		1	P102 to P106, P120, P125 to P127, P130,	2.7 V ≤ EVDD0 < 4.0 V			15.0	mA
			P140 to P145	1.8 V ≤ EVDD0 < 2.7 V			9.0	mA
his is the total upper limit of			(when duty ≤ 70% ^{Note 4})	1.6 V ≤ EVDD0 < 1.8 V			4.5	mA
he current that can flow hrough the relevant pins. Duty ≤ 70%" indicates the			Total of P05, P06, P10 to P17, P30, P31, P50 to P57, P60 to P67,	$4.0 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}$			80.0 Note 5	mA
bercentage of time during			P70 to P77, P80 to P87, P90 to P97, P100, P101,	2.7 V ≤ EVDD0 < 4.0 V			35.0	mA
which the current can flow.			P110 to P117, P146, P147 (when duty ≤ 70% ^{Note 4})	1.8 V ≤ EVDD0 < 2.7 V			20.0	mA
				1.6 V ≤ EVDD0 < 1.8 V			10.0	mA
			Total of all pins (when duty ≤ 70% Note 4)				150.0 Note 6	mA

40 to + 400% 40 c V < 50% - 50% - 50% - 50%/**T**.

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Guaranteed values of characteristics and values that users should adhere to

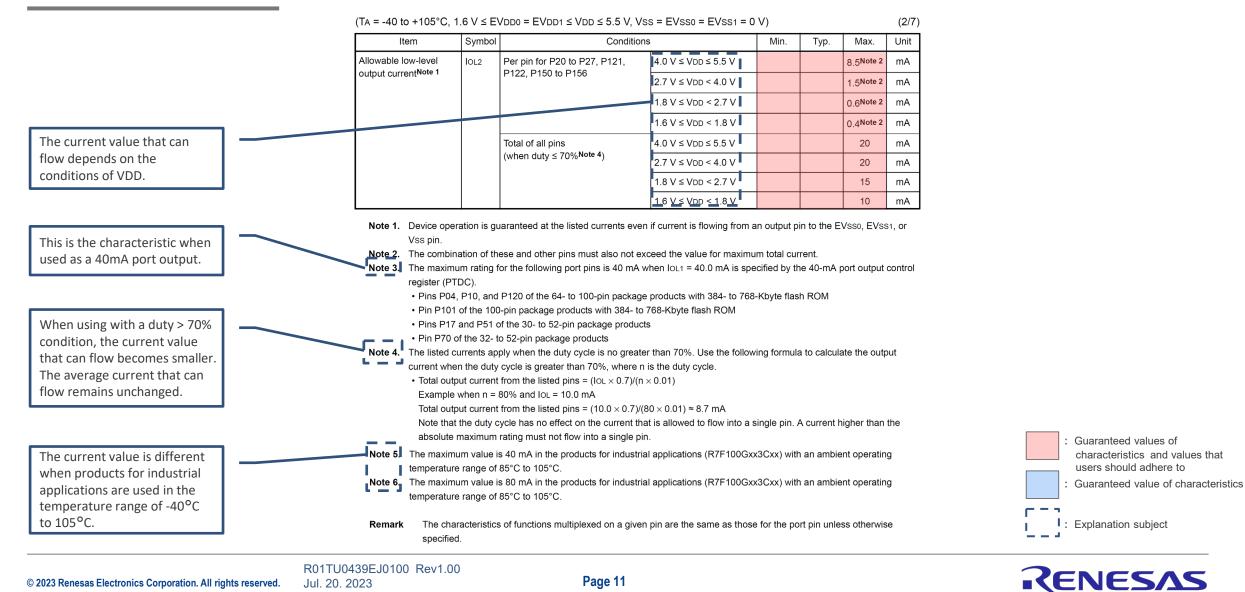
: Guaranteed value of characteristics

: Explanation subject

(Notes and Remark continue on the next page.)



DC CHARACTERISTICS **PIN CHARACTERISTICS** (4)



DC CHARACTERISTICS PIN CHARACTERISTICS (5)

This is the weltage range in		(TA = -40 to +105°C,	1.6 V ≤ E'	$VDD0 = EVDD1 \le VDD \le 5.5 \text{ V}, $	/ss = EVss0 = EVss1 =	0 V)			(3/7)
This is the voltage range in which the read value of the	$\overline{}$	Item	Symbol	Conditior	าร	Min.	Тур.	Max.	Unit
port register reliably becomes "1".		Input voltage, high	VIH1	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P140 to P147	Normal input buffer	0.8 EVDD0		EVDD0	V
			VIH2	P01, P03, P04, P10, P11, P13 to P17, P43, P44,	TTL input buffer 4.0 V ≤ EVDD0 ≤ 5.5 V	2.2		EVDD0	V
The characteristics change when set as a TTL input buffer.				P53 to P55, P80, P81, P142, P143	TTL input buffer 3.3 V ≤ EVDD0 < 4.0 V	2.0		EVDD0	V
					TTL input buffer 1.6 V ≤ EVDD0 < 3.3 V	1.5		EVDD0	V
P60-P63 are pins with a			Vінз	P20 to P27, P150 to P156		0.7 Vdd		Vdd	V
voltage withstand capability of 6V.			VIH4	P60 to P63		0.7 EVDD0		6.0	V
			VIH5	P121 to P124, P137, EXCLK, EX	, P137, EXCLK, EXCLKS, RESET			Vdd	V

The maximum value of VIH of pins P00, P02 to P04, P10 to P15, P17, P34, P42 to P45, P50, P52 to P55, P71, P72, Caution P74, P80 to P83, P96, P120, and P142 to P144 is EVDD0, even in the N-ch open-drain mode.

Guaranteed values of characteristics and values that users should adhere to : Guaranteed value of characteristics



DC CHARACTERISTICS 6

	(1A = -40 to)	$+105^{\circ}C, 1.6 V \le E$	$VDD0 = EVDD1 \le VDD \le 5.5 V,$	VSS = EVSS0 = EVSS1 =	U V)			(3/7
This is the voltage range in	Iter	m Symbol	Conditio	ons	Min.	Тур.	Max.	Unit
which the read value of the port register reliably becomes "0".	Input voltage	a, low VIL1	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P140 to P147	Normal input buffer	0		0.2 EVDD0	V
The characteristics change when set as a TTL input buffer.	_	VIL2	VIL2 P01, P03, P04, P10, P11, P13 to P17, P43, P44, P53 to P55, P80, P81, P142, P143	TTL input buffer 4.0 V ≤ EVDD0 ≤ 5.5 V	0		0.8	V
				TTL input buffer 3.3 V ≤ EVDD0 < 4.0 V	0		0.5	V
				TTL input buffer 1.6 V ≤ EVDD0 < 3.3 V	0		0.32	V
		VIL3	P20 to P27, P150 to P156		0		0.3 VDD	V
		VIL4	P60 to P63		0		0.3 EVDD0	V
		VIL5	P121 to P124, P137, EXCLK, E	XCLKS, RESET	0		0.2 Vdd	V

(TA = -40 to +105°C, 1.6 V ≤ EVDD0 = EVDD1 ≤ VDD ≤ 5.5 V, Vss = EVss0 = EVss1 = 0 V)

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Guaranteed values of characteristics and values that users should adhere to
Guaranteed value of characteristics

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DC CHARACTERISTICS PIN CHARACTERISTICS (7)

This is the voltage value		Item	Symbol	Conditi	ions	Min.	Тур.	Max.	Unit
output from the pin during high-level output. The voltage value varies depending on the		Output voltage, high	Vон1	P00 to P07, P10 to P17, P30 to P37, P40 to P47,	4.0 V ≤ EVDD0 ≤ 5.5 V, IOH1 = -10.0 mA	EVDD0 - 1.5			V
conditions of IOH.				P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106,	$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ IOH1 = -3.0 mA	EVDD0 - 0.7			V
		P110 to P117, P120, P125 to P127, P130, P140 to P147	2.7 V ≤ EVDD0 ≤ 5.5 V, Іон1 = -2.0 mA	EVDD0 - 0.6			V		
				1.8 V ≤ EVDD0 ≤ 5.5 V, Іон1 = -1.5 mA	EVDD0 - 0.5			V	
				1.6 V ≤ EVDD0 < 5.5 V, Іон1 = -1.0 mA	EVDD0 - 0.5			V	
			Vон2	P20 to P27, P121, P122, P150 to P156	4.0 V ≤ VDD ≤ 5.5 V, IOH2 = -3.0 mA	Vdd - 0.7			V
				2.7 V ≤ V _{DD} < 4.0 V, IOH2 = -1.0 mA	Vdd - 0.5			V	
					1.8 V ≤ VDD < 2.7 V, Іон2 = -1.0 mA	Vdd - 0.5			V
					$1.6 \text{ V} \le \text{V}_{\text{DD}} < 1.8 \text{ V},$ IOH2 = -0.5 mA	VDD - 0.5			V

Guaranteed values of characteristics and values that users should adhere to : Guaranteed value of characteristics

Caution P00, P02 to P04, P10 to P15, P17, P34, P42 to P45, P50, P52 to P55, P71, P72, P74, P80 to P83, P96, P120, and P142 to P144 do not output high-level signals in the N-ch open-drain mode.



DC CHARACTERISTICS ®

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 1.6 \text{ V} \le \text{EVDD0} = \text{EVDD1} \le \text{VDD} \le 5.5 \text{ V}, \text{Vss} = \text{EVss0} = \text{EVss1} = 0 \text{ V})$

		Item	Symbol		Conditions		Min.	Тур.	Max.	Unit
This is the veltage value		Output voltage, low	Vol1	P00 to P07, P10 to P17,	$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V}$	IOL1 = 20.0 mA			1.3	V
This is the voltage value output from the pin during				P30 to P37, P40 to P47, P50 to P57, P64 to P67,		IOL1 = 40.0 mANote			1.3	V
low-level output. The voltage				P70 to P77, P80 to P87, P90 to P97, P100 to P106,	4.0 V ≤ EVDD0 ≤ 5.5 V	IOL1 = 8.5 mA			0.7	V
value varies depending on the				P110 to P117, P120, P125 to P127, P130,		IOL1 = 17.0 mANote			0.7	V
conditions of IOL.				P140 to P147	2.7 V ≤ EVDD0 ≤ 5.5 V	IOL1 = 3.0 mA			0.6	V
-						IOL1 = 6.0 mA ^{Note}			0.6	V
					2.7 V ≤ EVDD0 ≤ 5.5 V	IOL1 = 1.5 mA			0.4	V
						IOL1 = 3.0 mA ^{Note}			0.4	V
					1.8 V ≤ EVDD0 ≤ 5.5 V	IOL1 = 0.6 mA			0.4	V
						IOL1 = 1.2 mA ^{Note}			0.4	V
					1.6 V ≤ EVDD0 ≤ 5.5 V	IOL1 = 0.3 mA			0.4	V
						IOL1 = 0.6 mA ^{Note}			0.4	V
			Vol2	P20 to P27, P121, P122,	4.0 V ≤ VDD ≤ 5.5 V, IOL	2 = 8.5 mA			0.7	V
				P150 to P156	2.7 V ≤ VDD < 4.0 V, IOL2 = 1.5 mA				0.5	V
					1.8 V ≤ VDD < 2.7 V, IOL	2 = 0.6 mA			0.4	V
					$1.6 \text{ V} \le \text{V}_{\text{DD}} < 1.8 \text{ V}, \text{ IOL}$	2 = 0.4 mA			0.4	V
			Vol3		4.0 V ≤ EVDD0 ≤ 5.5 V, I	ol3 = 15.0 mA			2.0	V
					4.0 V ≤ EVDD0 ≤ 5.5 V, I	ol3 = 5.0 mA			0.4	V
					2.7 V ≤ EVDD0 ≤ 5.5 V, I	OL3 = 3.0 mA			0.4	V
					1.8 V ≤ EVDD0 ≤ 5.5 V, I	OL3 = 2.0 mA			0.4	V
	1.6	1.6 V ≤ EVDD0 ≤ 5.5 V, I	OL3 = 1.0 mA			0.4	V			

Note The listed value applies when IoL1 = 40.0 mA is specified for the following port pins by the 40-mA port output control register (PTDC).

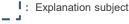
• Pins P04, P10, and P120 of the 64- to 100-pin package products with 384- to 768-Kbyte flash ROM

Pin P101 of the 100-pin package products with 384- to 768-Kbyte flash ROM

Pins P17 and P51 of the 30- to 52-pin package products

Pin P70 of the 32- to 52-pin products

 : Guaranteed values of characteristics and values that users should adhere to
 : Guaranteed value of characteristics



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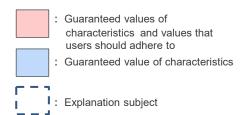


DC CHARACTERISTICS (9)

This is the value of the current that can flow when the output current control function is enabled. If an external resistance is connected, the current is limited by the limiting resistor.

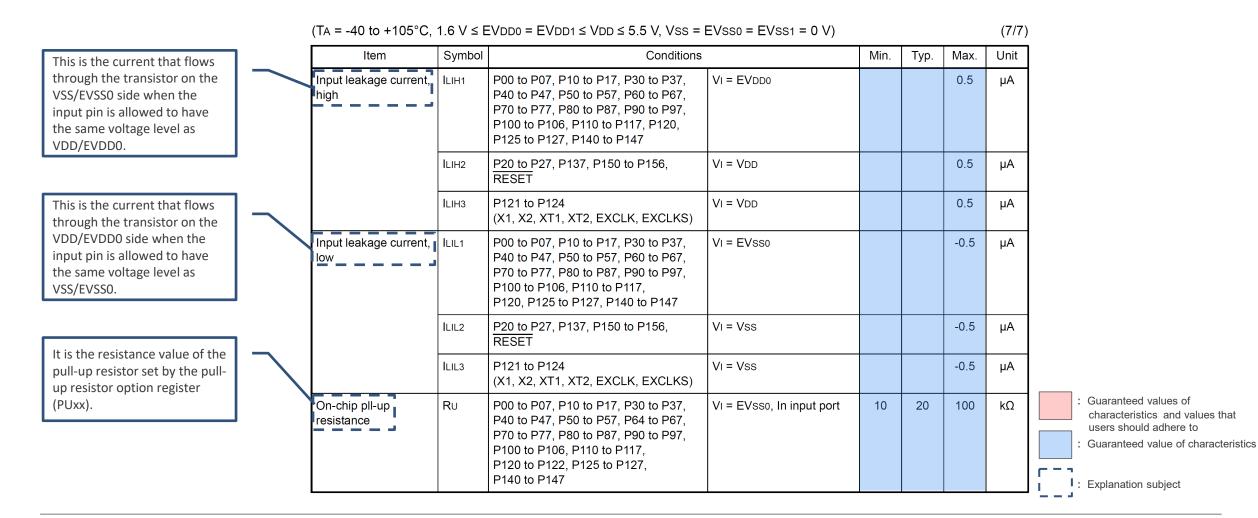
	(TA = -40 to +105°C, 1	.6 V ≤ EV0	$DD0 = EVDD1 \le VDD \le$	≦ 5.5 V, Vss = I	EVsso = EVss1 = 0 V)				(6/7)
[Item	Symbol		Conditions		Min.	Тур.	Max.	Unit
	Output current ^{Note}	CCDIOL	P16, P17, P50, P51	CCSm = 01H	$4.0 \text{ V} \leq \text{EV}$ DD $0 \leq 5.5 \text{ V}$	1.0	1.8	2.6	mA
			P60 to P63		2.7 V ≤ EVDD0 < 4.0 V	0.8	1.5	2.3	mA
				CCSm = 02H	$4.0 \text{ V} \leq \text{EVDD0} \leq 5.5 \text{ V}$	3.0	4.9	6.5	mA
					3.0 V ≤ EVDD0 < 4.0 V	2.7	4.3	5.9	mA
				CCSm = 03H	$4.0 \text{ V} \leq \text{EVDD0} \leq 5.5 \text{ V}$	6.6	10.0	13.2	mA
					3.3 V ≤ EVDD0 < 4.0 V	6.0	9.1	12.1	mA
			P60 to P63	CCSm = 04H	$4.0 \text{ V} \leq \text{EVDD0} \leq 5.5 \text{ V}$	10.2	15.0	19.8	mA
					3.3 V ≤ EVDD0 < 4.0 V	9.4	13.8	18.2	mA

Note The listed currents apply when the output current control function is enabled.





DC CHARACTERISTICS





DC CHARACTERISTICS SUPPLY CURRENT CHARACTERISTICS ①

This is the total current flowing through VDD and	$\overline{}$				products with 96- to $EVDD0 \le VDD \le 5.5$ V	/, Vss = EVsso = 0 V)						(1/4))
EVDD.		Item	Symbol			Conditions			Min.	Тур.	Max.	Unit	
		Supply	IDD1	Operating		fiH = 32 MHzNote 2	Basic	VDD = 5.0 V		1.3	—	mA	
		Current		mode	(high-speed main) mode		operation	VDD = 1.8 V		1.3	_		
					1		Normal	VDD = 5.0 V		3.0	5.0	mA	
		ſ					operation	VDD = 1.8 V		3.0	5.0		
he operating mode indicates he CPU's operating state.					18	fiH = 24 MHzNote 2	Normal	VDD = 5.0 V		2.3	3.8	mA	
					(low-speed main) mode		operation	VDD = 1.8 V		2.3	3.8		
						fiH = 16 MHzNote 2	Normal	VDD = 5.0 V		1.7	2.7	mA	
The value of the current	\checkmark				i :		operation	VDD = 1.8 V		1.7	2.7		
flowing through the CPU					1 i	fIM = 4 MHzNote 3	Normal	VDD = 5.0 V		0.4	0.7	mA	
varies depending on its processing.					1 1		operation	VDD = 1.6 V		0.4	0.7		
processing.					LP	fim = 2 MHzNote 3	Normal	VDD = 5.0 V		200	325	μA	
					(low-power main) mode		operation	VDD = 1.6 V		200	325		
The current value flowing						fim = 1 MHzNote 3	Normal	VDD = 5.0 V		112	178	μA	
through depends on the flash							operation	VDD = 1.6 V		111	176		: Guaranteed values of characteristics and values that
operating mode.					HS	fMX = 20 MHzNote 4,	Normal	VDD = 5.0 V		1.9	3.2	mA	users should adhere to : Guaranteed value of characterist
					(high-speed main) mode	Square wave input	operation	VDD = 1.8 V		1.9	3.2		
		(Rema	Irks are liste	ed on the ne									L I: Explanation subject
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DC CHARACTERISTICS SUPPLY CURRENT CHARACTERISTICS 2

	(TA = -40) to +105°(C, 1.6 V ≤ E	EVDD0 ≤ VDD ≤ 5.5 '	V, Vss = EVsso = 0 V)						(1/4)	
	Item	Symbol			Conditions			Min.	Тур.	Max.	Unit	
	Supply	IDD1	Operating		f _{MX} = 20 MHz ^{Note 4} ,	Normal	VDD = 5.0 V		1.8	3.0	mA	
	current Note 1		mode	(low-speed main) mode	Square wave input	operation	VDD = 1.8 V		1.7	3.0		
					fMX = 20 MHzNote 4,	Normal	VDD = 5.0 V		1.9	3.2	mA	
					Resonator connection	operation	VDD = 1.8 V		1.9	3.2		
The value of the current		Τ			fMX = 10 MHzNote 4,	Normal	VDD = 5.0 V		0.9	1.6	mA	
flowing varies depending on					Square wave input	operation	VDD = 1.8 V		0.9	1.6		
the CPU clock used.					fmx = 10 MHzNote 4,	Normal	VDD = 5.0 V		1.0	1.7	mA	
					Resonator connection	operation	VDD = 1.8 V		1.0	1.7		
					fMX = 8 MHzNote 4,	Normal	VDD = 5.0 V		0.8	1.3	mA	
					Square wave input	operation	VDD = 1.8 V		0.7	1.3		
					f _{MX} = 8 MHzNote 4,	Normal	VDD = 5.0 V		0.9	1.4	mA	
These are the specified					Resonator connection	operation	VDD = 1.8 V		0.8	1.4		
conditions for the power supply current.	Note 1	I. The liste	d currents a	re the total currents fl	owing into VDD and EVD	oo, including	the input leaka	age curr	ents flov	ving whe	en the	
	1				o or Vss, EVsso. The cur							
	1.			-	ito the A/D converter, LVI mory is being rewritten.	D circuit, I/O	port, and on-cr	ιιρ pull-ι	ip/pull-a	own res	listors,	
	Note 2				beed system clock, middl	e-speed on-o	chip oscillator,	low-spe	ed on-c	hip oscil	llator,	: Guaranteed values of characteristics and values that
	i -		-	are stopped.								users should adhere to
	Note 3		d currents a em clock are		eed on-chip oscillator, hi	gh-speed sys	stem clock, low	/-speed	on-chip	oscillato	or, and	: Guaranteed value of characteristics
	Note 4				peed on-chip oscillator, m	niddle-speed	on-chip oscilla	tor, low-	-speed o	on-chip		L Explanation subject
				stem clock are stoppe		·	·		-			
	R01TU0	439EJ0100	Rev1.00									
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DC CHARACTERISTICS SUPPLY CURRENT CHARACTERISTICS ③

ax. Unit	o. Mi	Min.			Conditions			Symbol	Item		
5.5 µA	2 5		TA = -40°C	Normal	fsub = 32.768 kHzNote 2,	Subsystem	Operating	IDD1	Supply		
5.8	5 5		TA = +25°C	operation	Low-speed on-chip oscillator operation	clock operation mode	mode		current Note 1		
8.5	8 8		TA = +50°C								
3.8	4 13		TA = +70°C								
2.1	3 22		TA = +85°C								
0.9	7 40		TA = +105°C								
5.6 µA	2 5		TA = -40°C	Normal	,						
5.7	4 5		TA = +25°C	operation							
8.5	7 8		TA = +50°C	TA = +50°							
3.7	3 13		TA = +70°C								
1.4	2 2'		TA = +85°C								
9.0	6 39		TA = +105°C							7	
5.2 μA	2 5		TA = -40°C	Normal	fsub = 32.768 kHz ^{Note 3} ,						f the value varies significantly
5.4	4 5		TA = +25°C	operation	Resonator connection						lepending on the ambient emperature, the ambient
.7	7 7		TA = +50°C								emperature will be included
3.4	3 13		TA = +70°C								s a specified condition.
0.9	2 20		TA = +85°C							_	
8.5	7 38		TA = +105°C								

(TA = -40 to +105°C, 1.6 V ≤ EVDD0 ≤ VDD ≤ 5.5 V, VSS = EVSS0 = 0 V)

Note 1. The listed currents are the total currents flowing into VDD and EVDD0, including the input leakage currents flowing when the level of the input pin is fixed to VDD, EVDD0 or Vss, EVss0. The currents in the Max. column include the peripheral operation current, but do not include those flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors, and those flowing while the data flash memory is being rewritten.

- Note 2. The listed currents apply when the high-speed on-chip oscillator, middle-speed on-chip oscillator, high-speed system clock, and subsystem clock are stopped. They do not include the current flowing into the RTC, 32-bit interval timer, and watchdog timer.
- Note 3. The listed currents apply when the high-speed on-chip oscillator, high-speed system clock, middle-speed on-chip oscillator, and low-speed on-chip oscillator are stopped, and the low power consumption oscillation 3 is specified (AMPHS1, AMPHS0 = 1, 1). They do not include the currents flowing into the RTC, 32-bit interval timer, and watchdog timer.

Guaranteed values of characteristics and values that users should adhere to Guaranteed value of characteristics

: Explanation subject

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DC CHARACTERISTICS SUPPLY CURRENT CHARACTERISTICS ④

This is the current flowing into		(TA = -40 to +105)	°C, 1.6 V ≤	$EVDD0 = EVDD1 \leq VDD$:	≤ 5.5 V, Vss = EVss0 = EVss1 = 0 V)				(1/2
VDD when the peripheral		Item	Symbol		Conditions	Min.	Тур.	Max.	Unit
functions are operational.	J	High-speed on- chip oscillator operating current	∣ _{FIH} Note 1				380		μA
The watchdog timer operating current includes the low-		Middle-speed on- chip oscillator operating current	∣ _{FIM} Note 1				20		μA
speed on-chip oscillator clock operating current.		Low-speed on- chip oscillator operating current	_{FIL} Note 1				0.3		μA
		RTC operating	IRTC	fRTCCLK = 32.768 kHz			0.005		μA
This is the current flowing into		current	Notes 1, 2, 3	fRTCCLK = 128 Hz			0.002		μA
the AVREFP pin.		32-bit interval timer operating current	li⊤ Notes 1, 2, 4				0.04		μA
This is the current flowing when selecting the internal	$ \neg \rangle$	Watchdog timer operating current	IWDT Notes 1, 2, 5	fı∟ = 32.768 kHz (typ.)			0.32		μA
reference voltage as the +	$ \setminus \rangle$	A/D converter		When conversion at	Normal mode, AVREFP = VDD = 5.0 V		0.95	1.6	mA
side reference voltage of the A/D converter or when		operating current	Notes 1, 6	maximum speed	Low voltage mode, AVREFP = VDD = 3.0 V		0.5	0.75	mA
selecting the internal reference voltage as the A/D	$ \setminus$	AVREFP current	IADREF Note 7	AVREFP = 5.0 V			52		μA
conversion target.		A/D converter internal reference voltage current	IADREF Note 1				114		μA
This is the current flowing when selecting the temperature sensor output		Temperature sensor operating current	ITMPSNote 1				110		μA
voltage as the A/D conversion target.		(Notes and Rem	arks continue	e on the next page.)					

 Guaranteed values of characteristics and values that users should adhere to
 Guaranteed value of characteristics

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: Explanation subject

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4. Peripheral Functions (Common to all products)

DC CHARACTERISTICS SUPPLY CURRENT CHARACTERISTICS (5)

	Item	Symbol		Conditions	Min.	Тур.	Max.	Unit
	D/A converter operating current	IDAC Notes 1, 8	Per channel			150		μA
	Comparator operating current	ICMP Notes 1, 9				6		μA
YP. value represents the ge current. The MAX.	LVD operating current	ILVD0 Notes 1, 10				0.02		μA
represents the num current that flows		ILVD1 Notes 1, 10				0.02		μA
entarily.	Self-programming operating current	IFSP Notes 1, 11				2.5	12.2	mA
	Data flash rewrite operating current	IBGO Notes 1, 12				2.5	12.2	mA
e values do not include	SNOOZE mode sequencer	ISMS Notes 1, 13	fін = 32 MHz	30- to 64-pin package products with 96- to 128-Kbyte flash ROM		1.1		mA
urrent flowing through IDD2, and IDD3.	operating current			30- to 64-pin package products with 192- to 256-Kbyte flash ROM and 80-pin package product with 128- to 256-Kbyte flash ROM		1.1		
				44- to 80-pin package products with 384- to 768-Kbyte flash ROM and 100- to 128-pin package products		1.4		
			fı∟ = 32.768 kHz	30- to 64-pin package products with 96- to 128-Kbvte flash ROM		1.2		μA
ne average current when Iting various sequencer ssing commands.				30- to 64-pin package products with 192- to 256-Kbyte flash ROM and 80-pin package product with 128- to 256-Kbyte flash ROM		1.2		
				44- to 80-pin package products with 384- to 768-Kbyte flash ROM and 100- to 128-pin package products		1.6		

 Guaranteed values of characteristics and values that users should adhere to
 Guaranteed value of characteristics

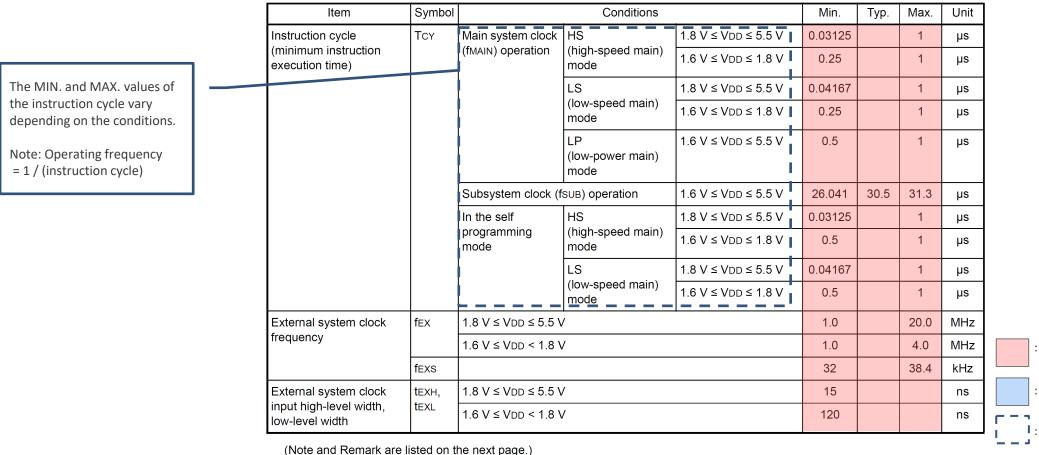
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AC CHARACTERISTICS 1

37.4 AC Characteristics

R01TU0439EJ0100 Rev1.00



(TA = -40 to +105°C, 1.6 V \leq EVDD0 = EVDD1 \leq VDD \leq 5.5 V, VSS = EVSS0 = EVSS1 = 0 V)

characteristics and values that users should adhere toGuaranteed value of characteristics

Guaranteed values of

: Explanation subject

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AC CHARACTERISTICS 2

	Item	Symbol	Conditio	ons	Min.	Тур.	Max.	Unit
	TI00 to TI07, TI10 to TI17 input high-level width, low-level width	t⊤iH, t⊤iL			1/fмск + 10			_{NS} Note
	TO00 to TO07, TO10 to	fto	HS (high-speed main) mode	4.0 V ≤ EVDD0 ≤ 5.5 V			16	MHz
	TO17 output frequency		LS (low-speed main) mode	2.7 V ≤ EVDD0 < 4.0 V			8	MHz
The MIN. and MAX. values of				1.8 V ≤ EVDD0 < 2.7 V			4	MHz
the output frequency vary				1.6 V ≤ EVDD0 < 1.8 V			2	MHz
depending on the power supply voltage.			LP (low-power main) mode	1.6 V ≤ EVDD0 ≤ 5.5 V			2	MHz
	PCLBUZ0, PCLBUZ1	fPCL	HS (high-speed main) mode	4.0 V ≤ EVDD0 ≤ 5.5 V			16	MHz
The MIN. and MAX. values of	output frequency		LS (low-speed main) mode	2.7 V ≤ EVDD0 < 4.0 V			8	MHz
the output frequency vary				1.8 V ≤ EVDD0 < 2.7 V			4	MHz
depending on the power				1.6 V ≤ EVDD0 < 1.8 V			2	MHz
supply voltage.			LP (low-power main) mode	1.6 V ≤ EVDD0 < 1.8 V			2	MHz
	Interrupt input high-level	finth,	INTP0	1.6 V ≤ VDD ≤ 5.5 V				μs
	width, low-level width	fintl	INTP1 to INTP11	1.6 V ≤ EVDD0 ≤ 5.5 V	1			μs
The MIN. value indicates the	Key interrupt input low-	fkrh,	KR0 to KR7	1.8 V ≤ EVDD0 ≤ 5.5 V	250			ns
	level width	fkrl		1.6 V ≤ EVDD0 < 1.8 V	1			μs
	RESET low-level width	frsl			10			μs
reliably detectable range. MIN. There is a possibility of detecting signals even below the MIN. value.	RESET low-level width	fRSL condition			┃ 1 ┃ ■_10_■			-

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 1.6 \text{ V} \le \text{EVDD0} = \text{EVDD1} \le \text{VDD} \le 5.5 \text{ V}, \text{ Vss} = \text{EVss0} = \text{EVss1} = 0 \text{ V})$

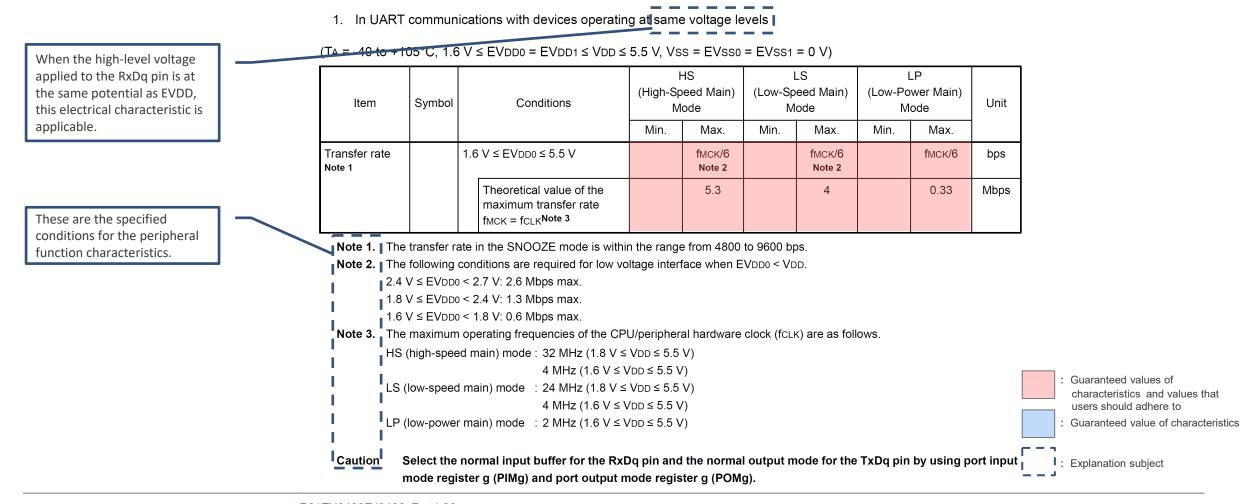
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Guaranteed values of characteristics and values that users should adhere to Guaranteed value of characteristics



CHARACTERISTICS OF THE PERIPHERAL FUNCTIONS SERIAL ARRAY UNIT 1

37.5.1 Serial array unit



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CHARACTERISTICS OF THE PERIPHERAL FUNCTIONS SERIAL ARRAY UNIT 2

2. In simplified SPI (CSI) communications in the master mode with devices operating at same voltage levels with the

internal SCKp clock (the ratings below are only applicable to CSI00)

(TA = -40 to +85°C, 2.7 V ≤ EVDD0 = EVDD1 ≤ VDD ≤ 5.5 V, Vss = EVss0 = EVss1 = 0 V)

Item	Symbol	C	Conditions	HS (High-Spee Mode		LS (Low-Spee Mod		LP (Low-Powe) Mod		Uni
				Min.	Max.	Min.	Max.	Min.	Max.	
SCKp cycle time	tксү1	tĸcγ1 ≥ 2/fcLĸ	$4.0 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}$	62.5		83.3		1000		ns
			2.7 V ≤ EVDD0 ≤ 5.5 V			125		1000		ns
SCKp high-/ low-level width	tĸнı, tĸ∟ı	4.0 V ≤ EVDD0	≤ 5.5 V	tксү1/2 - 7		tксү1/2 - 10		tксү1/2 - 50		ns
		2.7 V ≤ EVDD0	≤ 5.5 V	tксү1/2 - 10		tксү1/2 - 15		tксү1/2 - 50		ns
SIp setup time	tsik1	4.0 V ≤ EVDD0	≤ 5.5 V	23		33		110		ns
(to SCKp↑) ^{Note 1}		2.7 V ≤ EVDD0 ≤ 5.5 V		33		50		110		ns
SIp hold time (from SCKp↑) Note 1	tKSI1	2.7 V ≤ EVDD0 ≤ 5.5 V		10		10		10		ns
Delay time from SCKp↓ to SOp output ^{Note 2}	tKSO1	C = 20 pFNote	3		10		10		10	ns
become 1 and C Note 2. This se output P Note 3. C is the	tting applies when DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The setting for the SIp setup times "to SCKp↓" and that for the SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPm CKPmn = 0. tting applies when DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The setting for the delay time to Se becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The setting for the delay time to Se becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0. et the normal input buffer for the SIp pin and the normal output mode for the SOp pin and SCKp pin by us port input mode register g (PIMg) and the port output mode register g (POMg).									°mn o SO

applied to the SIp pin is at the same potential as EVDD, this electrical characteristic is applicable. CSI00 allows for a faster transfer rate compared to other channels. However, different conditions for the power supply voltage apply.

When the high-level voltage

These are the specified conditions for the peripheral function characteristics.

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Guaranteed values of

: Explanation subject

characteristics and values that users should adhere to

Guaranteed value of characteristics

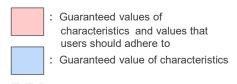
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CHARACTERISTICS OF THE PERIPHERAL FUNCTIONS SERIAL ARRAY UNIT ③

5. In simplified I²C communications with devices operating at same voltage levels

$(TA = -40 \text{ to } +105^{\circ}\text{C}, 1.6 \text{ V} \le \text{EVDD0} = \text{EVDD1} \le \text{VDD} \le 5.5 \text{ V}, \text{ Vss} = \text{EVss0} = \text{EVss1} = 0 \text{ V})$

(1/2)LΡ HS LS (High-Speed Main) (Low-Speed Main) (Low-Power Main) Conditions Unit Item Symbol Mode Mode Mode Min Max. Min Max. Min Max. SCLr clock frequency fscL $2.7 \text{ V} \leq \text{EVDD0} \leq 5.5 \text{ V},$ 400Note 1 kHz 1000 1000 $C_b = 50 \text{ pF}, R_b = 2.7 \text{ k}\Omega$ Note 1 Note 1 $1.8 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}.$ 400Note 1 400Note 1 400Note 1 kHz $C_{b} = 100 \text{ pF}$. $R_{b} = 3 \text{ k}\Omega$ $1.8 V \le EVDD0 < 2.7 V.$ 300Note 1 300Note 1 300Note 1 kHz $C_b = 100 \text{ pF}$. $R_b = 5 \text{ k}\Omega$ $1.6 V \le EVDD0 < 1.8 V.$ 250Note 1 250Note 1 250Note 1 kHz $C_b = 100 \text{ pF}, R_b = 5 \text{ k}\Omega$ $2.7 V \le EVDD0 \le 5.5 V.$ Hold time when SCLr 475 475 1150 tLOW ns $C_b = 50 \text{ pF}$. $R_b = 2.7 \text{ k}\Omega$ is low $1.8 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V},$ 1150 1150 1150 ns $C_b = 100 \text{ pF}, R_b = 3 \text{ k}\Omega$ $1.8 V \le EVDD0 < 2.7 V.$ 1550 1550 1550 ns $C_b = 100 \text{ pF}, R_b = 5 \text{ k}\Omega$ $1.6 V \le EVDD0 < 1.8 V$, 1850 1850 1850 ns $C_b = 100 \text{ pF}$. $R_b = 5 \text{ k}\Omega$ Hold time when SCLr | thigh $2.7 \text{ V} \leq \text{EVDD0} \leq 5.5 \text{ V},$ 475 475 1150 ns $C_b = 50 \text{ pF}, R_b = 2.7 \text{ k}\Omega$ is high $1.8 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V},$ 1150 1150 1150 ns $C_b = 100 \text{ pF}, R_b = 3 \text{ k}\Omega$ $1.8 V \le EVDD0 < 2.7 V.$ 1550 1550 1550 ns $C_b = 100 \text{ pF}, R_b = 5 \text{ k}\Omega$ $1.6 V \le EVDD0 < 1.8 V$, 1850 1850 1850 ns $C_b = 100 \text{ pF}, R_b = 5 \text{ k}\Omega$



(Notes and Caution are listed on the next page, and Remarks are listed on the page after the next page.)





CHARACTERISTICS OF THE PERIPHERAL FUNCTIONS SERIAL ARRAY UNIT (4)

5. In simplified I²C communications with devices operating at same voltage levels

(TA = -40 to +105°C, 1.6 V ≤ EVDD0 = EVDD1 ≤ VDD ≤ 5.5 V, VSS = EVSS0 = EVSS1 = 0 V)

(2/2)

Item	Symbol	Conditions	HS (High-Spe Moo	ed Main)	LS (Low-Spe Mod	ed Main)	LF (Low-Pow Mo	er Main)	Unit
			Min.	Max.	Min.	Max.	Min.	Max.	
Data setup time (reception)	tsu:dat	$2.7 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ $C_{\text{b}} = 50 \text{ pF}, \text{ R}_{\text{b}} = 2.7 \text{ k}\Omega$	1/fмск + 85 Note 2		1/fмск + 85 Note 2		1/fMCK + 145 Note 2		ns
		$\begin{array}{l} 1.8 \ V \leq EV_{DD0} \leq 5.5 \ V, \\ C_b = 100 \ pF, \ R_b = 3 \ k\Omega \end{array}$	1/fмск + 145 Note 2		1/fмск + 145 Note 2		1/fмск + 145 Note 2		ns
		$\begin{array}{l} 1.8 \ V \leq EV \mbox{DD0} < 2.7 \ V, \\ C_b = 100 \ pF, \ R_b = 5 \ k\Omega \end{array}$	1/fмск + 230 Note 2		1/fмск + 230 Note 2		1/fмск + 230 Note 2		ns
		$1.6 V \le EV_{DD0} < 1.8 V,$ $C_b = 100 \text{ pF}, R_b = 5 \text{ k}\Omega$	1/fмск + 290 Note 2		1/fмск + 290 Note 2		1/fMCK + 290 Note 2		ns
Data hold time (transmission)	thd:dat	$2.7 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ Cb = 50 pF, Rb = 2.7 k Ω	0	305	0	305	0	305	ns
		1.8 V ≤ EVDD0 ≤ 5.5 V, Cb = 100 pF, Rb = 3 kΩ	0	355	0	355	0	355	ns
		1.8 V ≤ EVDD0 < 2.7 V, Cb = 100 pF, Rb = 5 kΩ	0	405	0	405	0	405	ns
		1.6 V ≤ EVDD0 < 1.8 V, Cb = 100 pF, Rb = 5 kΩ	0	405	0	405	0	405	ns

Note 1. The listed times must be no greater than fMCK/4.

Note 2. Set fMCK so that it will not exceed the hold time when SCLr is low or high.

Caution Select the normal input buffer and the N-ch open drain output (withstand voltage of VDD (when 30- to 52-pin products)/withstand voltage of EVDD (when 64- to 128-pin products)) mode for the SDAr pin and the normal output mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register h (POMh).

 Guaranteed values of characteristics and values that users should adhere to
 Guaranteed value of characteristics



CHARACTERISTICS OF THE PERIPHERAL FUNCTIONS SERIAL INTERFACE UARTA

37.5.2 Serial interface UARTA

(TA = -40 to +105°C, 1.6 V \leq EVDD0 = EVDD1 \leq VDD \leq 5.5 V, Vss = EVss0 = EVss1 = 0 V)

Item	Symbol	Conditions	Min.	Тур.	Max.	Unit
Transfer rate			200	0	153600	bps

Caution Select the normal input buffer for the RxDq pin and the normal output mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg).

 Guaranteed values of characteristics and values that users should adhere to
 Guaranteed value of characteristics

 Explanation subject



CHARACTERISTICS OF THE PERIPHERAL FUNCTIONS SERIAL INTERFACE IICA

1. I²C standard mode

Item	Symbol	Conditions	Min.	Тур.	Max.	Unit
SCLA0 clock frequency	fscl	Standard mode: fc∟κ ≥ 1 MHz	0		100	kHz
Setup time of restart condition	tsu:sta		4.7			μs
Hold time ^{Note 1}	thd:sta		4.0			μs
Hold time when SCLA0 is low	tLOW		4.7			μs
Hold time when SCLA0 is high	tніgн		4.0			μs
Data setup time (reception)	tsu:dat		250			ns
Data hold time (transmission) ^{Note 2}	thd:dat		0		3.45	μs
Setup time of stop condition	tsu:sto		4.0			μs
Bus-free time	tBUF		4.7			μs

 $(TA = -40 \text{ to } +105^{\circ}\text{C}, 1.6 \text{ V} \le \text{EVDD0} = \text{EVDD1} \le \text{VDD} \le 5.5 \text{ V}, \text{Vss} = \text{EVss0} = \text{EVss1} = 0 \text{ V})$

Note 1. The first clock pulse is generated after this period when the start or restart condition is detected.

Note 2. The maximum value of the transfer of the clock stretching will be inserted on reception of an acknowledgment (ACK) signal.

Caution The listed frequency and times apply even when bit 2 (PIOR2) in the peripheral I/O redirection register (PIOR) is 1. In such cases, the pin characteristics (IOH1, IOL1, VOH1, VOL1) must satisfy the values in the redirect destination. Guaranteed values of characteristics and values that users should adhere to
 Guaranteed value of characteristics



ANALOG CHARACTERISTICS (1)

37.6.1 A/D converter characteristics

1. Normal modes 1 and 2

(TA = -40 to +105°C, 2.4 V \leq AVREFP \leq VDD \leq 5.5 V, VSS = 0 V,

reference voltage (+) = AVREFP (ADREFP1 = 0, ADREFP0 = 1), reference voltage (-) = AVREFM (ADREFM = 1), target pins: ANI2 to ANI14, internal reference voltage, and temperature sensor output voltage)

Item	Symbol		Conditions	Min.	Тур.	Max.	Unit
Resolution	RES			8		12	Bit
Conversion clock	fad			1		32	MHz
Overall errorNotes 1, 3, 4, 5	AINI	12-bit resolution	$4.5 \text{ V} \leq \text{AV}_{\text{REFP}} = \text{V}_{\text{DD}} \leq 5.5 \text{ V}$			±7.5	LSB
			$2.7 \text{ V} \leq \text{AV}_{\text{REFP}} = \text{V}_{\text{DD}} \leq 5.5 \text{ V}$			±9.0	LSB
-			$2.4 \text{ V} \leq \text{AV}_{\text{REFP}} = \text{V}_{\text{DD}} \leq 5.5 \text{ V}$			±9.0	LSB
Conversion time ^{Note 6}	tCONV	12-bit resolution	$4.5 \text{ V} \leq \text{AV}_{\text{REFP}} = \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	2.0			μs
			$2.7 \text{ V} \leq \text{AV}_{\text{REFP}} = \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	2.0			μs
			$2.4 \text{ V} \leq \text{AV}_{\text{REFP}} = \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	2.0			μs
Zero-scale errorNotes 1, 2, 3, 4, 5	Ezs	12-bit resolution	$4.5 \text{ V} \leq \text{AV}_{\text{REFP}} = \text{V}_{\text{DD}} \leq 5.5 \text{ V}$			±0.17	%FSR
			$2.7 \text{ V} \leq \text{AVREFP} = \text{VDD} \leq 5.5 \text{ V}$			±0.21	%FSR
			$2.4 \text{ V} \leq \text{AV}_{\text{REFP}} = \text{V}_{\text{DD}} \leq 5.5 \text{ V}$			±0.21	%FSR
Full-scale errorNotes 1, 2, 3, 4, 5	Efs	12-bit resolution	$4.5 \text{ V} \leq \text{AV}_{\text{REFP}} = \text{V}_{\text{DD}} \leq 5.5 \text{ V}$			±0.17	%FSR
			$2.7 \text{ V} \leq \text{AV}_{\text{REFP}} = \text{V}_{\text{DD}} \leq 5.5 \text{ V}$			±0.21	%FSR
			$2.4 \text{ V} \leq \text{AV}_{\text{REFP}} = \text{VDD} \leq 5.5 \text{ V}$			±0.21	%FSR

 Guaranteed values of characteristics and values that users should adhere to
 Guaranteed value of characteristics

Explanation subject

(Note and Remark are listed on the next page.)

The total error (LSB) at 10-bit resolution is obtained by dividing it by $4 (= 2^{(12-10)})$.

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ANALOG CHARACTERISTICS

A/D CONVERTER CHARACTERISTICS ②

(TA = -40 to +105°C, 2.4 V \leq AVREFP \leq VDD \leq 5.5 V, Vss = 0 V,

reference voltage (+) = AVREFP (ADREFP1 = 0, ADREFP0 = 1), reference voltage (-) = AVREFM (ADREFM = 1), target pins: ANI2 to ANI14, internal reference voltage, and temperature sensor output voltage)

Item	Symbol		Conditions	Min.	Тур.	Max.	Unit
Integral linearity errorNotes 1, 4, 5	ILE	12-bit resolution	$4.5 \text{ V} \leq \text{AVREFP} = \text{VDD} \leq 5.5 \text{ V}$			±3.0	LSB
			$2.7 \text{ V} \leq \text{AV}_{\text{REFP}} = \text{V}_{\text{DD}} \leq 5.5 \text{ V}$			±3.0	LSB
			$2.4 \text{ V} \leq \text{AVREFP} = \text{VDD} \leq 5.5 \text{ V}$			±3.0	LSB
Differential linearity errorNote 1	DLE	12-bit resolution	$4.5 \text{ V} \leq \text{AVREFP} = \text{VDD} \leq 5.5 \text{ V}$		±1.0		LSB
			$2.7 \text{ V} \leq \text{AV}_{\text{REFP}} = \text{VDD} \leq 5.5 \text{ V}$		±1.0		LSB
			$2.4 \text{ V} \leq \text{AV}_{\text{REFP}} = \text{VDD} \leq 5.5 \text{ V}$		±1.0		LSB
Analog input voltage	VAIN			0		AVREFP	V

The characteristics vary depending on factors such as the selected analog input channel and other conditions. Note 1. This value does not include the quantization error (±1/2 LSB).

Note 2. This value is indicated as a ratio (%FSR) to the full-scale value.

Note 3. When pins ANI16 to ANI31 are selected as the target pins for conversion, the maximum values are as follows.

Overall error: Add ±3 LSB to the maximum value.

Zero-scale/full-scale error: Add ±0.04%FSR to the maximum value.

Note 4. When reference voltage (+) = VDD and reference voltage (-) = Vss, the maximum values are as follows.

Overall error: Add ±10 LSB to the maximum value.

Zero-scale/full-scale error: Add ±0.25%FSR to the maximum value.

Integral linearity error: Add ±4 LSB to the maximum value.

Note 5. When AVREFP < VDD, the maximum values are as follows.

Overall error/zero-scale error/full-scale error: Add (±0.75 LSB × (VDD voltage (V) - AVREFP voltage (V)) to the maximum

value.

Integral linearity error: Add (±0.2 LSB × (VDD voltage (V) - AVREFP voltage (V)) to the maximum value.

Note 6. When the internal reference voltage or the temperature sensor output voltage is selected as the target for conversion, the sampling time must be at least 5 µs. Accordingly, use standard mode 2 with the longer sampling time.

: Guaranteed values of characteristics and values that users should adhere to

: Guaranteed value of characteristics



ANALOG CHARACTERISTICS

TEMPERATURE SENSOR/INTERNAL REFERENCE VOLTAGE CHARACTERISTICS, D/A CONVERTER CHARACTERISTICS

37.6.2 Temperature sensor/internal reference voltage characteristics

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 1.8 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{V}_{SS} = 0 \text{ V})$

These are the characteristics
of the temperature sensor
output voltage that can be
specified as the A/D
conversion target.

These are the characteristics of the + side reference voltage of the A/D converter or the internal reference voltage that can be specified as the A/D conversion target.

Item	Symbol	Conditions	Min.	Тур.	Max.	Unit
Temperature sensor output voltage	VTMPS25	Setting ADS register = 80H, TA = +25°C		1.05		V
Internal reference voltage	Vbgr	Setting ADS register = 81H	1.42	1.48	1.54	V
Temperature coefficient	FVTMPS	Temperature dependency of the temperature sensor voltage		-3.3		mV/°C
Operation stabilization wait time	tamp		5			μs

37.6.3 D/A converter characteristics

Item	Symbol	C	onditions	Min.	Тур.	Max.	Unit	
Resolution	RES					8	Bit	
Overall error	AINL	Rload = 8 MΩ	$1.8 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$			± 2.5	LSB	: Guaranteed values of characteristics and values that
		Rload = 4 M Ω	$1.8 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$			± 2.5	LSB	users should adhere to : Guaranteed value of characteristics
Settling time	tset	Cload = 20 pF	$2.7 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$			3	μs	5.5.3
			$1.6 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$			6	μs	: Explanation subject

$(TA = -40 \text{ to } +105^{\circ}\text{C}, 1.6 \text{ V} \le \text{EVDD0} = \text{EVDD1} \le \text{VDD} \le 5.5 \text{ V}, \text{Vss} = \text{EVss0} = \text{EVss1} = 0 \text{ V})$

This is the time it takes for the set voltage to be output.

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ANALOG CHARACTERISTICS COMPARATOR CHARACTERISTICS

37.6.4 Comparator characteristics

Item	Symbol	Conditions	3	Min.	Тур.	Max.	Unit
Input voltage range	IVREF	Input to the IVREF0 and IVRE C0LVL = 0, C1LVL = 0	F1 pins	0		VDD - 1.4 and EVDD0	V
		Input to the IVREF0 and IVRE C0LVL = 1, C1LVL = 1	· · · · · · · · · · · · · · · · · · ·			EVDD0	V
	IVCMP	Input to the IVCMP0 and IVCM	1P1 pins	-0.3		EVDD0 + 0.3	V
Output delay	td	VDD = 3.0 V,	High-speed mode			1.5	μs
		Input slew rate > 1 V/µs	Low-speed mode		3.0		μs
Offset voltage	_	High-speed mode				50	mV
		Low-speed mode				40	mV
Operation stabilization wait time	tCMP			30			μs
Internal reference voltage	VBGR2			1.4		1.6	V

 Guaranteed values of characteristics and values that users should adhere to
 Guaranteed value of characteristics



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These are the characteristics of the internal reference

voltage that can be selected

as the reference voltage for

Comparator 0.

ANALOG CHARACTERISTICS POR CIRCUIT CHARACTERISTICS

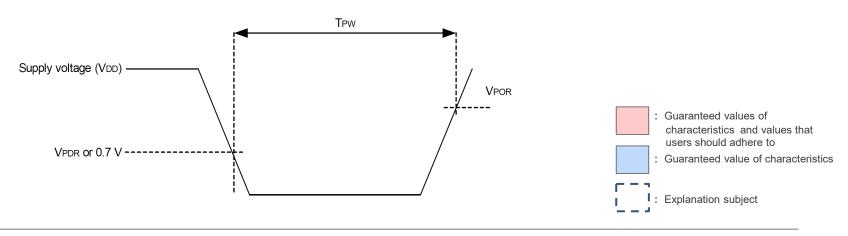
37.6.5 POR circuit characteristics

(TA = -40 to +105°C, Vss = 0 V)

Voltage fluctuations of less than 300us may not result in a reset occurring.

Item	Symbol	Conditions	Min.	Тур.	Max.	Unit
Detection voltage	VPOR, VPDR		1.43	1.50	1.57	V
Minimum pulse width ^{Note}	TPW		300			μs

Note This width is the minimum time required for a POR reset when VDD falls below VPDR. This width is also the minimum time required for a POR reset from when VDD falls below 0.7 V to when VDD exceeds VPOR in the STOP mode or while the main system clock is stopped through setting bit 0 (HIOSTOP) and bit 7 (MSTOP) in the clock operation status control register (CSC).



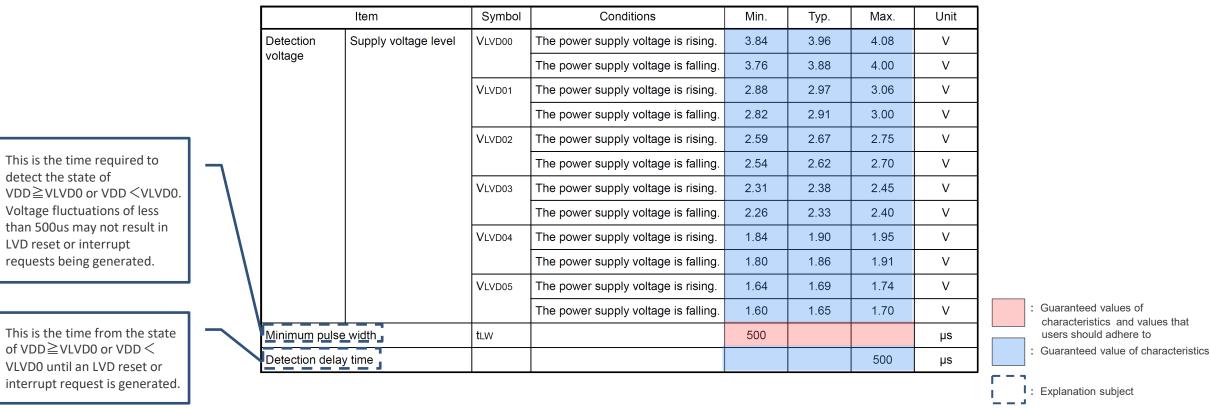


ANALOG CHARACTERISTICS LVD CIRCUIT CHARACTERISTICS

37.6.6 LVD circuit characteristics

1. LVD0 Detection Voltage in the Reset Mode and Interrupt Mode

$(T_A = -40 \text{ to } +105^{\circ}\text{C}, \text{ VPDR} \le \text{VDD} \le 5.5 \text{ V}, \text{ Vss} = 0 \text{ V})$
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ANALOG CHARACTERISTICS POWER SUPPLY VOLTAGE RISING SLOPE CHARACTERISTICS

37.6.7 Power supply voltage rising slope characteristics

(TA = -40 to +105°C, Vss = 0 V)

This is the specification for when power is turned on. It is not a specification for ripple voltage.

 ltem	Symbol	Conditions	Min.	Тур.	Max.	Unit
Power supply voltage rising slope	SVDD				54	V/ms

Caution Make sure to keep the internal reset state by the LVD0 circuit or an external reset until VDD reaches the operating voltage range shown in AC characteristics.

 Guaranteed values of characteristics and values that users should adhere to
 Guaranteed value of characteristics
 Explanation subject



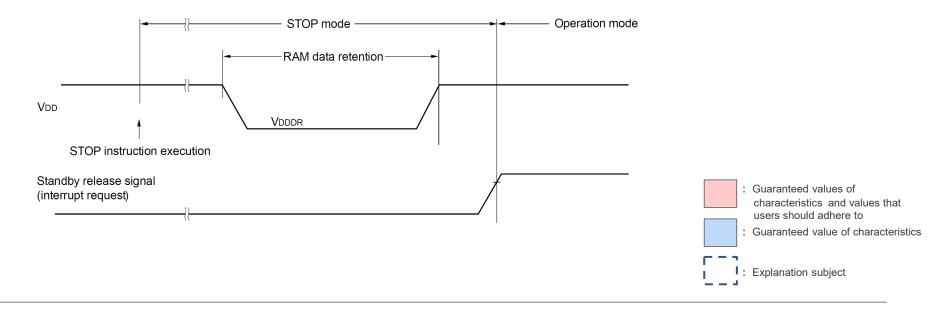
RAM DATA RETENTION CHARACTERISTICS

37.7 RAM Data Retention Characteristics

(TA = -40 to +105°C, Vss = 0V)

Item	Symbol	Conditions	Min.	Тур.	Max.	Unit
Data retention supply voltage	Vdddr		1.43Note		5.5	V

Note This voltage depends on the POR detection voltage. When the voltage drops, the data in RAM are retained until a POR is applied, but are not retained following a POR.





FLASH MEMORY PROGRAMMING CHARACTERISTICS 1

37.8 Flash Memory Programming Characteristics

Item	Symbol	Conditions	Min.	Тур.	Max.	Unit
CPU/peripheral hardware clock frequency	fclk		1		32	MHz
Number of code flash rewritesNotes 1, 2, 3	Cerwr	Retained for 20 years TA = 85°C	1,000			Times
Number of data flash rewritesNotes 1, 2, 3		Retained for 1 year TA = 25°C		1,000,000		
		Retained for 5 years TA = 85°C	100,000			
		Retained for 20 years TA = 85°C	10,000			

$(TA = -40 \text{ to } +105^{\circ}\text{C}, 1.6 \text{ V} \le \text{VDD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Note 1. 1 erase + 1 write after the erase is regarded as 1 rewrite. The retaining years are until next rewrite after the rewrite.

Note 2. The listed numbers of times apply when using flash memory programmer and Renesas Electronics self programming library.

Note 3. These are the characteristics of the flash memory and the results obtained from reliability testing by Renesas Electronics Corporation.

Guaranteed values of characteristics and values that users should adhere to
Guaranteed value of characteristics



FLASH MEMORY PROGRAMMING CHARACTERISTICS (2)

This is the characteristic of code flash memory during self-programming for rewriting. 1. Code flash memory

 $(TA = -40 \text{ to } +105^{\circ}\text{C}, 1.6 \text{ V} \le \text{VDD} \le 5.5 \text{ V}, \text{ Vss} = 0 \text{ V})$

ltem		Symbol	fc	ськ = 1 М	/Hz	fclk =	2 MHz,	3 MHz	4 MHz	≤ fCLK <	< 8 MHz	8 MHz	≤ fCLK <	32 MHz	fcl	к = 32 М	ИНz	Unit
item		Gymbol	Min.	Тур.	Max.	Min.	Тур.	Max.	Min.	Тур.	Max.	Min.	Тур.	Max.	Min.	Тур.	Max.	
Programming time	4 bytes	tP4	—	74.7	656.5	_	51.0	464.6	—	41.7	384.8	—	37.1	346.2	—	34.2	321.9	μs
Erasure time	2 Kbytes	tE2K	—	10.4	312.2	—	7.7	258.5	_	6.4	231.8	_	5.8	218.4	—	5.6	214.4	ms
Blank checking 4 bytes tBC4 time 2 Kbytes tBC2K	tBC4	—	_	38.4	_	—	19.2	_	_	13.1	_	_	10.2	_	_	8.3	μs	
	2 Kbytes	tвс2к	—	_	2618.9	_	_	1309.5	_	_	658.3	_	_	332.8	_	_	234.1	μs
Time taken to forcibly stop the erasure		tSED	—		18.0	—	—	14.0	—	—	12.0	—	—	11.0	—	—	10.3	μs
the erasure Security setting time		tawssas	—	18.2	526.2	—	14.4	469.2	—	12.5	441.1	—	11.6	427.1	_	11.3	422.6	ms
Time until progra starts following cancellation of th instruction			20	_	_	20			20	_	_	20	_	_	20	_	—	μs

Caution The listed values do not include the time until the operations of the flash memory start following execution of an instruction by software.

 Guaranteed values of characteristics and values that users should adhere to
 Guaranteed value of characteristics



FLASH MEMORY PROGRAMMING CHARACTERISTICS ③

2. Data flash memory

This is the characteristic of data flash memory during selfprogramming for rewriting.

ltem		Symbol	fC	ськ = 1 М	ИHz	fclk =	2 MHz,	3 MHz	4 MHz	≤ fCLK <	< 8 MHz	8 MHz	≤ fCLK <	32 MHz	fcL	к = 32 🛚	ИНz	Unit
item		Symbol	Min.	Тур.	Max.	Min.	Тур.	Max.	Min.	Тур.	Max.	Min.	Тур.	Max.	Min.	Тур.	Max.	
Programming 1 byte time 256 bytes		tP4	—	74.7	656.5	-	51.0	464.6	—	- 41.7	384.8	_	37.1	346.2	_	34.2	321.9	μs
Erasure time	256 bytes	tE2K		7.8	259.2	_	6.4	232.0	_	5.8	218.5	_	5.5	211.8	_	5.4	209.7	ms
Blank checking time	1 byte	tBC4			38.4	_		19.2	_		13.1	_		10.2	_		8.3	μs
	256 bytes	tвс2к	_	_	1326.1	_	_	663.1	_	_	335.1	_	_	171.2	_	_	121.0	μs
Time taken to forcibly stop the erasure		tSED	_	_	18.0	_	_	14.0	_	_	12.0	—	_	11.0	_	_	10.3	μs
Time until programming starts following cancellation of the STOP instruction			20	_	_	20	_	_	20	_	_	20	_	_	20	_	_	μs
Time until readir following setting to 1		_	0.25	—	—	0.25	—	—	0.25	—	—	0.25	—	—	0.25	—	—	μs

Caution The listed values do not include the time until the operations of the flash memory start following execution of an instruction by software.

 Guaranteed values of characteristics and values that users should adhere to
 Guaranteed value of characteristics

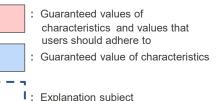


DEDICATED FLASH MEMORY PROGRAMMER COMMUNICATION (UART)

37.9 Dedicated Flash Memory Programmer Communication (UART)

This is the transfer rate when using the dedicated flash memory programmer (PG-FP6). (TA = -40 to +105°C, 1.8 V ≤ EVDD0 = EVDD1 ≤ VDD ≤ 5.5 V, VSS = EVSS0 = EVSS1 = 0 V)

Item	Symbol	Conditions	Min.	Тур.	Max.	Unit
Transfer rate		During serial programming	115,200		1,000,000	bps



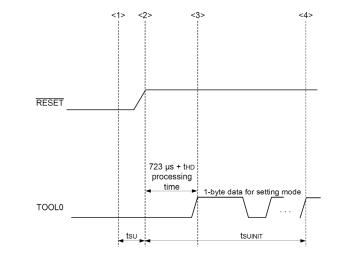


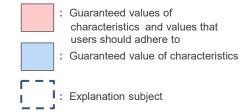
TIMING OF ENTRY TO FLASH MEMORY PROGRAMMING MODES

37.10 Timing of Entry to Flash Memory Programming Modes

Item	Symbol	Conditions	Min.	Тур.	Max.	Unit
Time to complete the communication for the initial setting after the external reset is released	tsuinit	POR and LVD reset must be released before the external reset is released.			100	ms
Time to release the external reset after the TOOL0 pin is set to the low level	ts∪	POR and LVD reset must be released before the external reset is released.	10			μs
Time to hold the TOOL0 pin at the low level after the external reset is released (the processing time of the firmware to control the flash memory is not included)	tнD	POR and LVD reset must be released before the external reset is released.	1			ms

$(T_A = -40 \text{ to } +105^{\circ}\text{C})$	$1.8 \text{ V} \le \text{EVDD0} = \text{EVDD1} \le \text{VDD} \le 5.5 \text{ V}, \text{Vss} = \text{EVss0} = \text{EVss1} = 0 \text{ V}$





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<1> The low level is input to the TOOL0 pin.

<2> The external reset is released. Note that the POR and LVD reset must be released before the external reset is released.

<3> The TOOL0 pin is set to the high level.

<4> Setting of the flash memory programming mode by UART reception and complete the baud rate setting.





